



P- Channel Enhancement-Mode Vertical DMOS FET

Features

- ▶ Low threshold (-2.0V max.)
- ▶ High input impedance
- ▶ Low input capacitance
- ▶ Fast switching speeds
- ▶ Low on-resistance
- ▶ Free from secondary breakdown
- ▶ Low input and output leakage
- ▶ Complementary N- and P-channel devices

Applications

- ▶ Logic level interfaces - ideal for TTL and CMOS
- ▶ Solid state relays
- ▶ Battery operated systems
- ▶ Photo voltaic drives
- ▶ Analog switches
- ▶ General purpose line drivers
- ▶ Telecom switches

General Description

This low threshold enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package Options			BV _{DSS} / BV _{DGS} (max) (V)	R _{DS(ON)} (max) (Ω)	V _{GS(th)} (max) (V)	I _{D(ON)} (min) (A)
	8-Lead SOIC	TO-92	Die*				
TP2640	TP2640LG-G	TP2640N3-G	TP2640ND	-400	15	-2.0	-0.7

* MIL visual screening available.
-G indicates package is RoHS compliant ('Green')



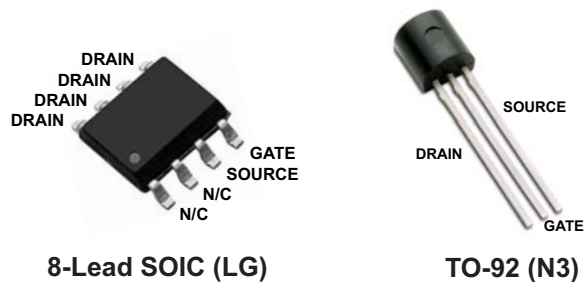
Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV _{DSS}
Drain-to-gate voltage	BV _{DGS}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	+300°C

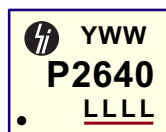
Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

* Distance of 1.6mm from case for 10 seconds.

Pin Configurations

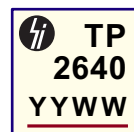


Product Marking



YY = Year Sealed
WW = Week Sealed
L = Lot Number
_____ = "Green" Packaging

8-Lead SOIC (LG)



YY = Year Sealed
WW = Week Sealed
_____ = "Green" Packaging

TO-92 (N3)

Thermal Characteristics

Package	I_D (continuous) [†] (mA)	I_D (pulsed) (A)	Power Dissipation @ $T_c = 25^\circ\text{C}$ (W)	θ_{jc} ($^\circ\text{C}/\text{W}$)	θ_{ja} ($^\circ\text{C}/\text{W}$)	I_{DR} [‡] (mA)	I_{DRM} (A)
8-Lead SOIC	-210	-1.25	1.3 [‡]	24	96 [‡]	-210	-1.25
TO-92	-180	-0.8	1.0	125	170	-180	-0.8

Notes:

[†] I_D (continuous) is limited by max rated T_j .

[‡] Mounted on FR4 board, 25mm x 25mm x 1.57mm

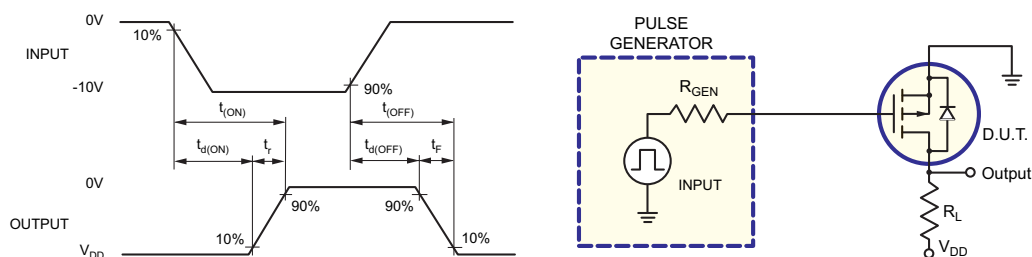
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	-400	-	-	V	$V_{GS} = 0V, I_D = -2.0mA$
$V_{GS(th)}$	Gate threshold voltage	-0.8	-	-2.0	V	$V_{GS} = V_{DS}, I_D = -1.0mA$
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-	5.0	mV/ $^\circ\text{C}$	$V_{GS} = V_{DS}, I_D = -1.0mA$
I_{GSS}	Gate body leakage	-	-	-100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
I_{DSS}	Zero gate voltage drain current	-	-	-1.0	μA	$V_{GS} = 0V, V_{DS} = -100V$
				-10.0		$V_{GS} = 0V, V_{DS} = \text{Max rating}$
				-1.0	mA	$V_{DS} = 0.8 \text{ Max Rating}, V_{GS} = 0V, T_A = 125^\circ\text{C}$
$I_{D(ON)}$	On-state drain current	0.7	-	-	A	$V_{GS} = -10V, V_{DS} = -25V$
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	12	15	Ω	$V_{GS} = -2.5V, I_D = -20mA$
			11	15		$V_{GS} = -4.5V, I_D = -150mA$
			11	15		$V_{GS} = -10V, I_D = -300mA$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	0.75	%/ $^\circ\text{C}$	$V_{GS} = -10V, I_D = -300mA$
G_{FS}	Forward transconductance	200	-	-	mmho	$V_{DS} = -25V, I_D = -300mA$
C_{ISS}	Input capacitance	-	-	300	pF	$V_{GS} = 0V, V_{DS} = -25V, f = 1.0MHz$
C_{OSS}	Common source output capacitance	-	-	50		
C_{RSS}	Reverse transfer capacitance	-	-	12		
$t_{d(ON)}$	Turn-on delay time	-	-	10	ns	$V_{DD} = -25V, I_D = -300MA, R_{GEN} = 25\Omega$
t_r	Rise time	-	-	15		
$t_{d(OFF)}$	Turn-off delay time	-	-	60		
t_f	Fall time	-	-	40		
V_{SD}	Diode forward voltage drop	-	-	-1.8	V	$V_{GS} = 0V, I_{SD} = -200mA$
t_{rr}	Reverse recovery time	-	300	-	ns	$V_{GS} = 0V, I_{SD} = -200MA$

Notes:

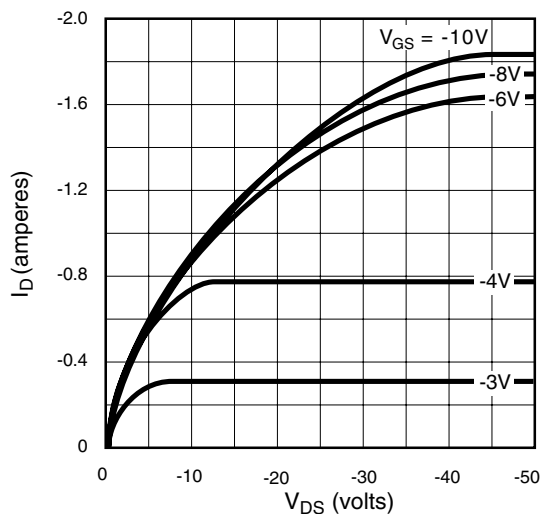
1. All D.C. parameters 100% tested at 25C unless otherwise stated. (Pulse test: 300s pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

N- Channel Switching Waveforms and Test Circuit

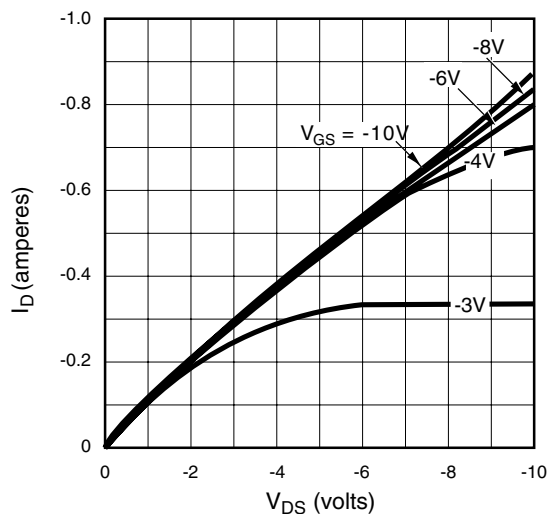


Typical Performance Curves

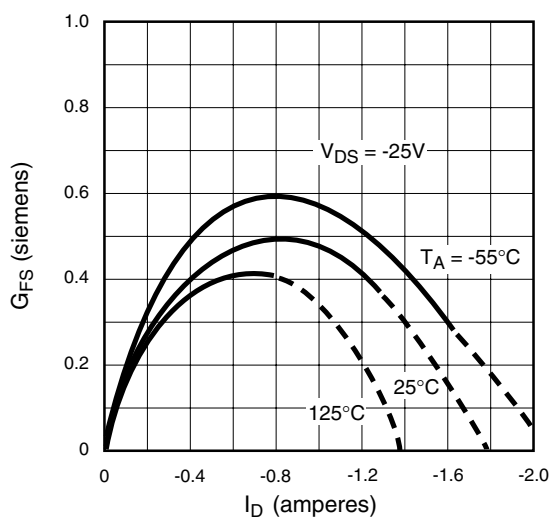
Output Characteristics



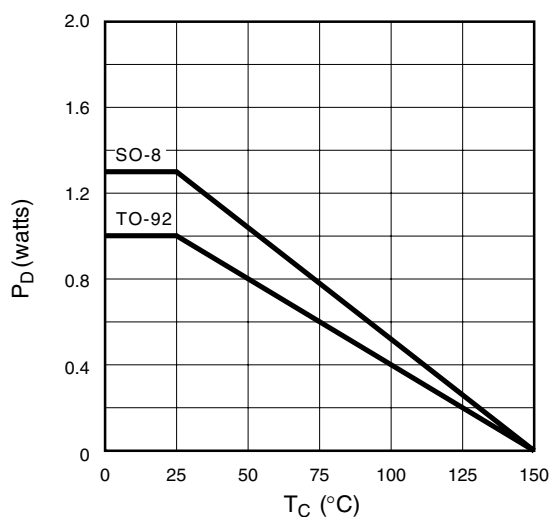
Saturation Characteristics



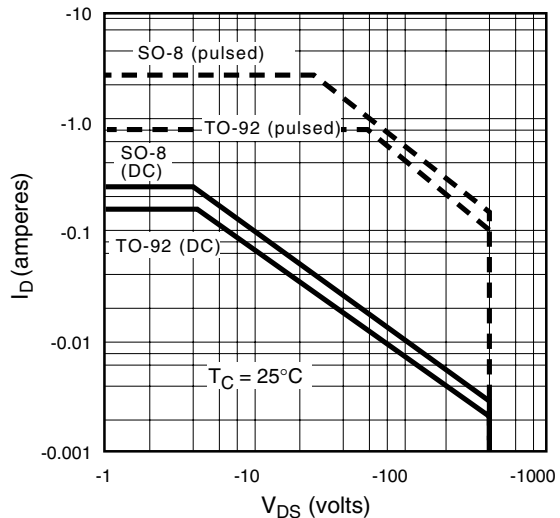
Transconductance vs. Drain Current



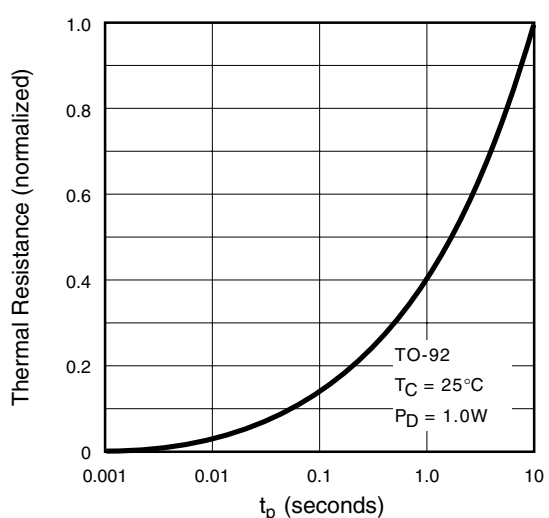
Power Dissipation vs. Temperature



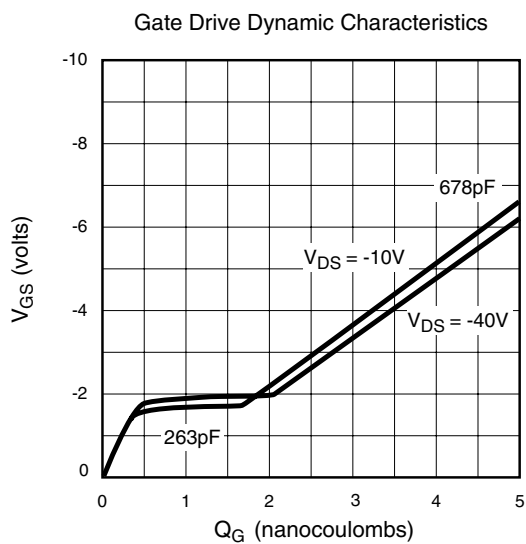
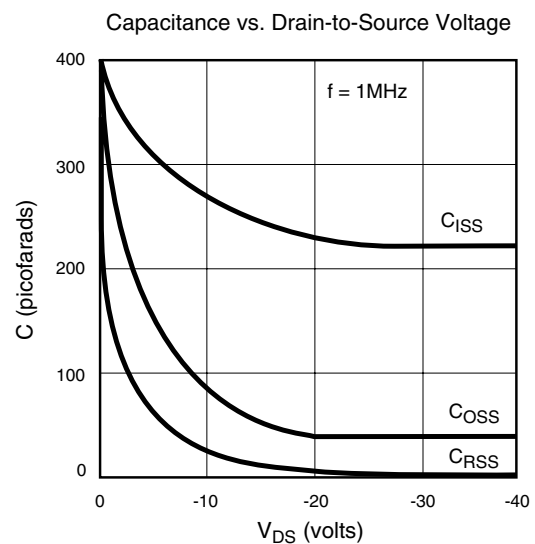
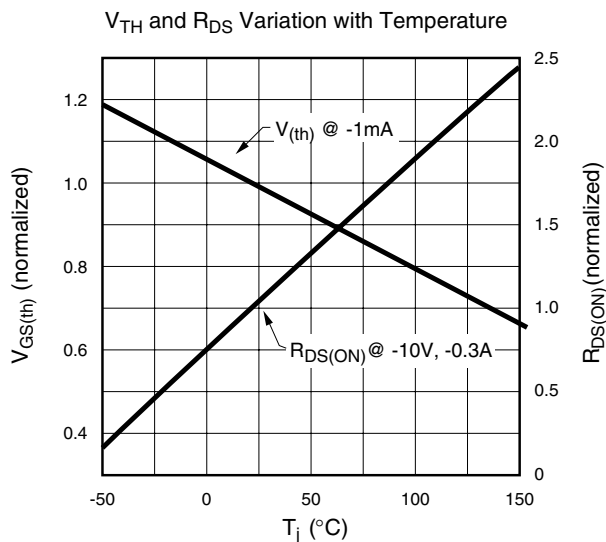
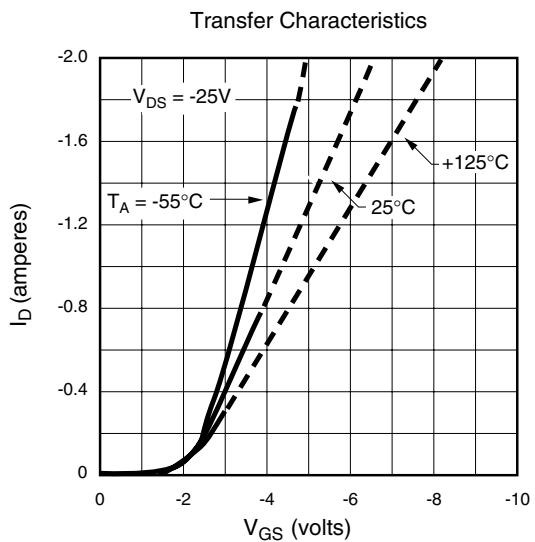
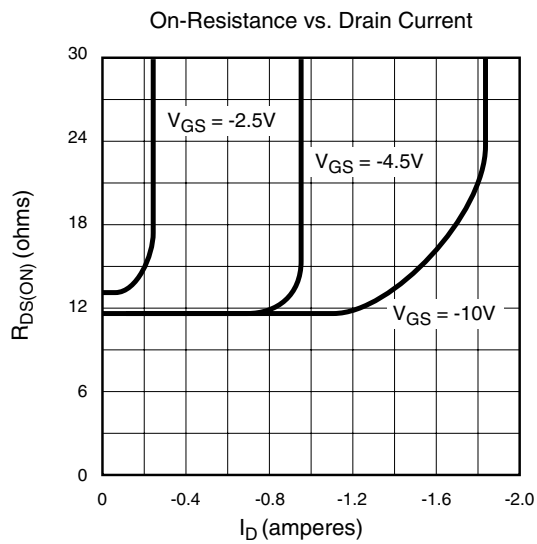
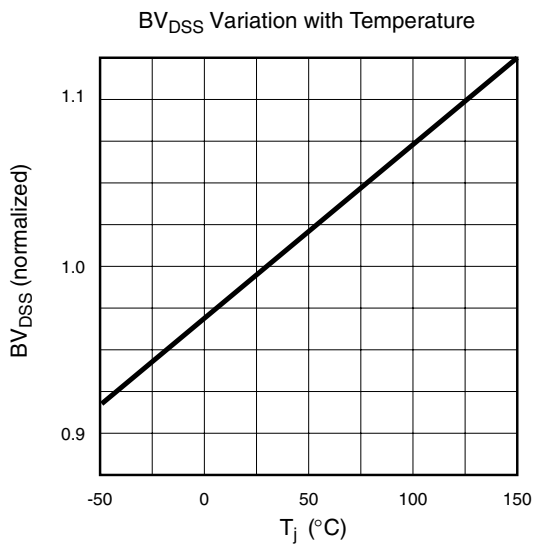
Maximum Rated Safe Operating Area



Thermal Response Characteristics

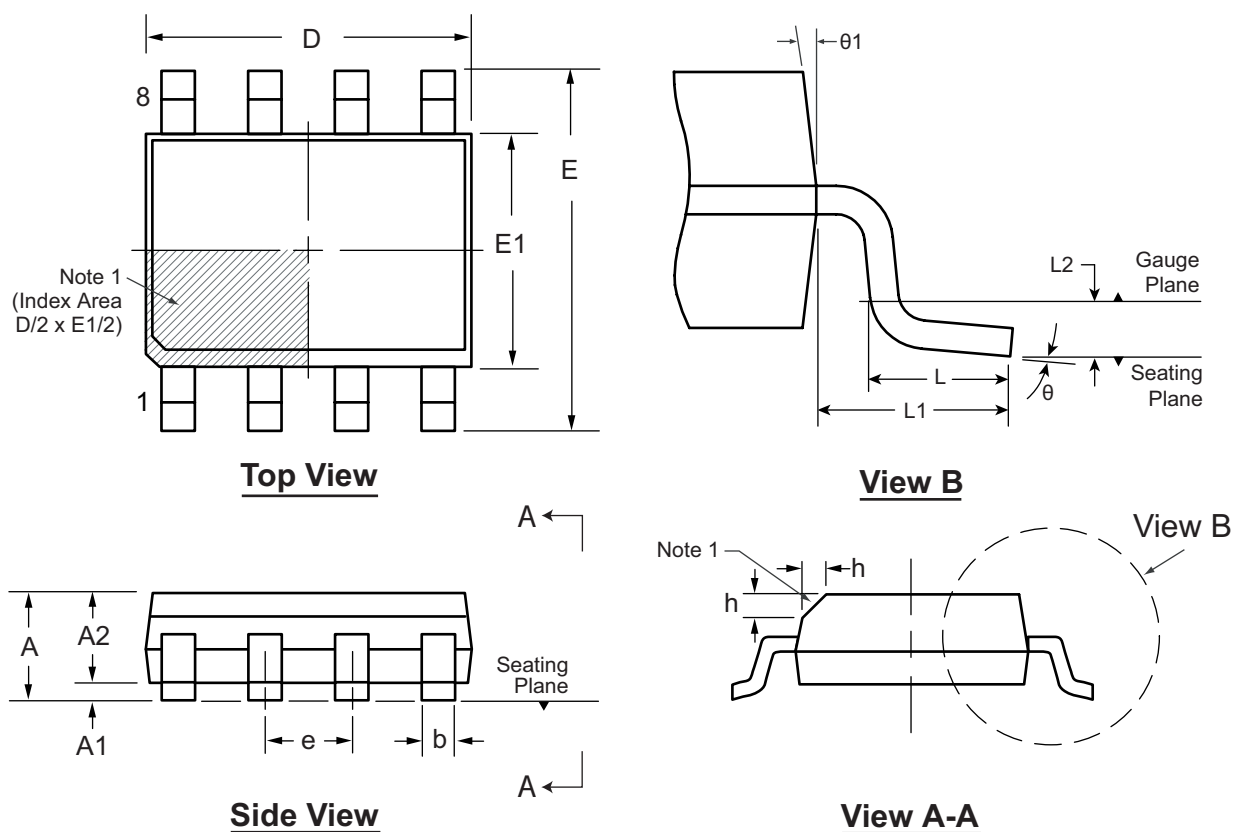


Typical Performance Curves (cont.)



8-Lead SOIC (Narrow Body) Package Outline (LG)

4.9x3.9mm body, 1.75mm height (max), 1.27mm pitch



Note 1:

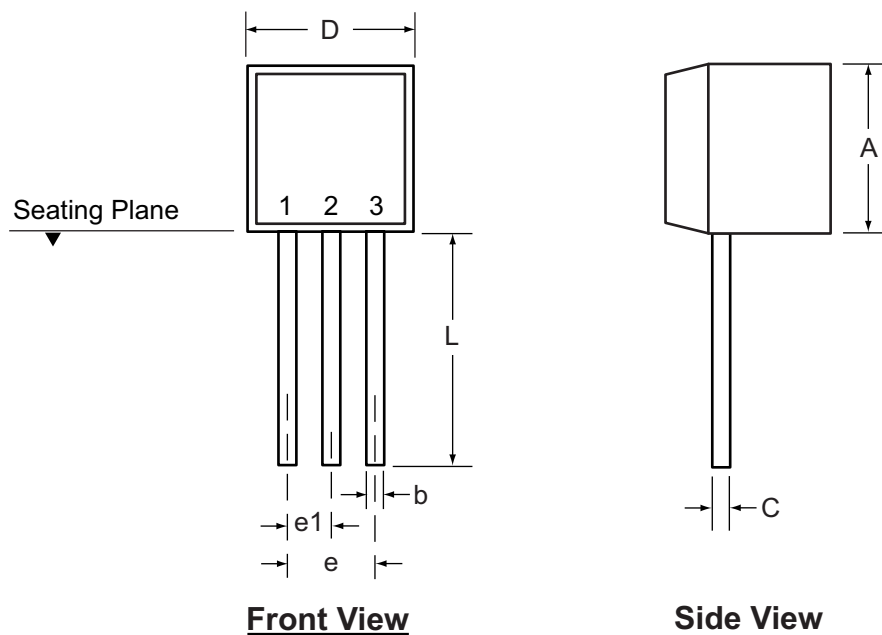
This chamfer feature is optional. If it is not present, then a Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier may be either a mold, or an embedded metal or marked feature.

Symbol		A	A1	A2	b	D	E	E1	e	h	L	L1	L2	θ	$\theta 1$
Dimension (mm)	MIN	1.35	0.10	1.25	0.31	4.80	5.80	3.80	1.27 BSC	0.25	0.40	1.04 REF	0.25 BSC	0°	5°
	NOM	-	-	-	-	4.90	6.00	3.90		-	-			-	-
	MAX	1.75	0.25	1.50	0.51	5.00	6.20	4.00		0.50	1.27			8°	15°

JEDEC Registration MS-012, Variation AA, Issue E, Sept. 2005.

Drawings not to scale.

3-Lead TO-92 Package Outline (N3)



Symbol		A	b	C	D	E	E1	e	e1	L
Dimension (inches)	MIN	.170	.014	.014	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022	.022	.205	.165	.105	.105	.055	-

Drawings not to scale.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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Supertex inc.
 1235 Bordeaux Drive, Sunnyvale, CA 94089
 TEL: (408) 222-8888 / FAX: (408) 222-4895
www.supertex.com